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MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGF1951A

Microwave Power MES FET (Leadless Ceramic Package)

DESCRIPTION

The MGF1951A is designed for use in S to Ku band power amplifiers.

The lead-less ceramic package assures minimum parasitic losses.

FEATURES

High gain and High P1dB

Glp=9.0dB, P1dB=13dBm (Typ.) @ f=12GHz

APPLICATION

S to Ku band power Amplifiers

QUALITY GRADE

GG

ORDERING INFORMATION

Tape & reel 3000pcs./reel

Outline Drawing

Fig.1

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V _{GDO}	Gate to drain voltage	-8	V
V_{GSO}	Gate to source voltage	-8	V
I _D	Drain current	120	mA
PT	Total power dissipation	300	mW
T _{ch}	Channel temperature	125	°C
T _{stg}	Storage temperature	-65 to +125	°C

Keep Safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum
effort into making semiconductor products better
and more reliable, but there is always the
possibility that trouble may occur with them.

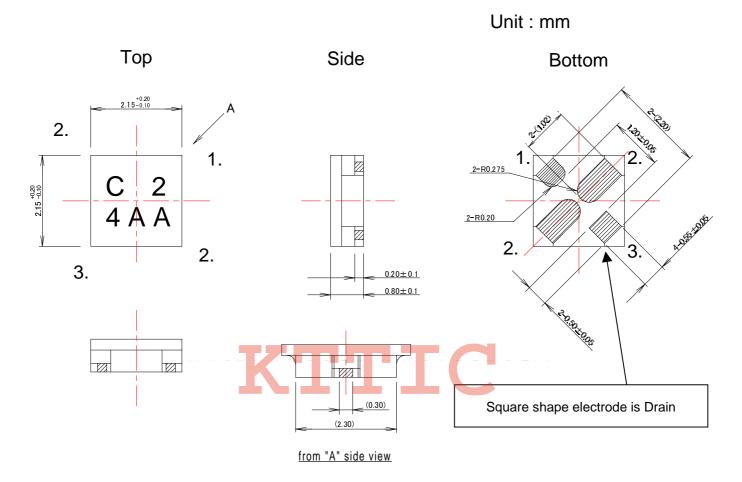
Trouble with semiconductors may lead to personal
injury, fire or property damage. Remember to give
due consideration to safety when making your
circuit designs, with appropriate measure such
as (I) placement of substitutive, auxiliary circuits,
(ii) use of non-flammable material or (iii) prevention
against any malfunction or mishap.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Synbol	Parameter	Test conditions	Limits		Unit	
			MIN.	TYP.	MAX	
V(BR)GDO	Gate to drain breakdown voltage	Ig=-30μA	-8	-15		V
IDSS	Saturated drain current	V _{GS} =0V,V _{DS} =3V	35	60	120	mA
V _{GS(off)}	Gate to source cut-off voltage	V _{DS} =3V,I _D =300μA	-0.3	-1.4	-3.5	V
P1dB	Output Power at 1dB gain	V _D S=3V,ID=30mA	11	13		dBm
	Compression	f=12GHz				
Glp	Linear Power Gain	V _{DS} =3V,ID=30mA	7	9		dB
		f=12GHz,Pin=-5dBm				

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Fig.1



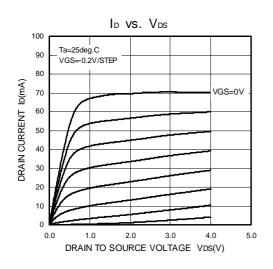
- 1. Gate
- 2. Source
- 3. Drain

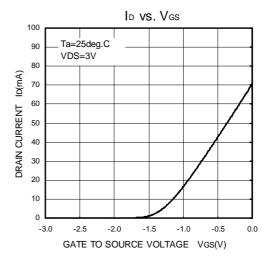


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Microwave Power MES FET (Leadless Ceramic Package)

TYPICAL CHARACTERISTICS (Ta=25°C)











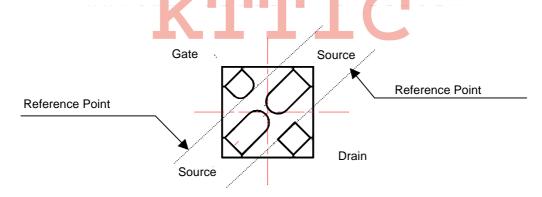
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Microwave Power MES FET (Leadless Ceramic Package)

S PARAMETERS

(Conditions: VDS=3V,ID=30mA,Ta=25deg.C)

f	S11		S21		S12		S22		K	MAG/MSG
(GHz)	Mag.	Angle	Mag.	Angle	Mag.	Angle	Mag.	Angle		(dB)
1	0.984	-17.7	4.239	163.2	0.016	78.2	0.581	-11.3	0.18	24.3
2	0.946	-38.6	4.103	144.3	0.031	64.3	0.565	-26.2	0.32	21.3
3	0.906	-52.5	3.914	131.2	0.043	54.3	0.548	-34.3	0.43	19.6
4	0.857	-71.1	3.710	115.9	0.054	44.2	0.518	-45.5	0.53	18.4
5	0.811	-85.3	3.445	103.3	0.061	35.6	0.509	-54.9	0.64	17.5
6	0.771	-97.4	3.197	92.5	0.065	29.6	0.500	-61.4	0.76	16.9
7	0.736	-109.8	2.984	81.7	0.069	23.7	0.502	-66.9	0.86	16.4
8	0.710	-121.6	2.847	70.7	0.071	19.0	0.507	-72.1	0.93	16.0
9	0.679	-133.6	2.737	60.4	0.075	15.1	0.509	-75.9	0.99	15.6
10	0.645	-146.3	2.659	20.1	0.083	11.3	0.513	-79.6	0.99	15.1
11	0.594	-159.8	2.600	39.5	0.089	2.6	0.496	-84.2	1.09	12.8
12	0.549	-175.7	2.570	28.4	0.091	-2.7	0.472	-87.2	1.19	11.9
13	0.508	165.8	2.532	16.2	0.095	-9.0	0.443	-91.4	1.27	11.1
14	0.481	142.3	2.480	2.5	0.100	-18.0	0.399	-96.7	1.34	10.5
15	0.472	116.9	2.378	-10.9	0.101	-26.7	0.342	-101.7	1.45	9.7
16	0.508	92.7	2.289	-23.8	0.103	-34.7	0.279	-107.6	1.47	9.4
17	0.573	70.4	2.160	-37.5	0.105	-42.9	0.211	-112.1	1.44	9.2
18	0.646	52.2	1.975	-51.6	0.103	-50.4	0.135	-115.3	1.44	8.9





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